

MSU2N60

600V N-Channel MOSFET

Description

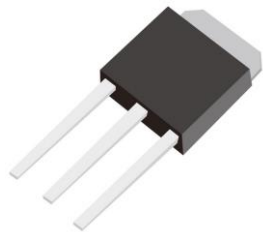
The MSU2N60 is a N-channel enhancement-mode MOSFET , providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-251 package is universally preferred for all commercial-industrial applications

Features

- Originative New Design
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge : 9.5nC (Typ.)
- Extended Safe Operating Area
- Lower RDS(ON) : 4.0 Ω (Typ.) @VGS=10V
- 100% Avalanche Tested
- RoHS compliant package

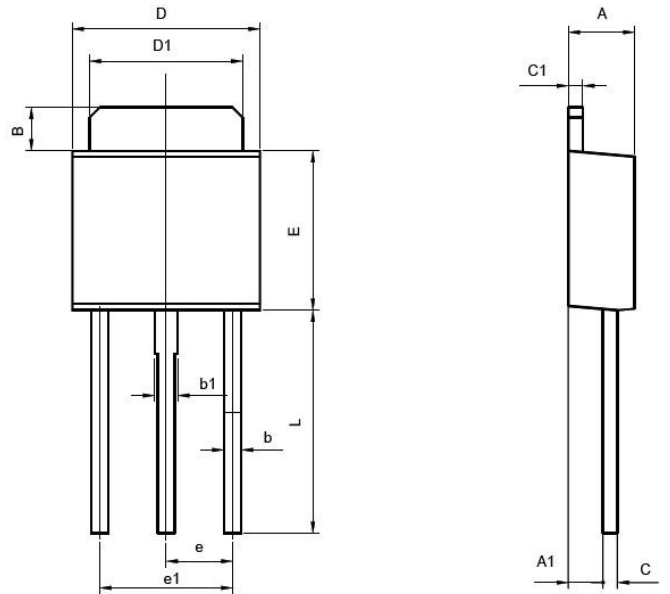
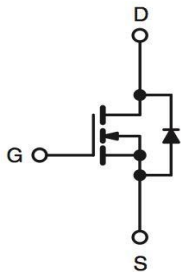
Packing & Order Information

80/Tube ; 4,000/Box



**RoHS
COMPLIANT**

Graphic symbol



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	min	max	min	max
A	2.15	2.45	0.85	0.96
A1	1.00	1.40	0.39	0.55
B	1.25	1.75	0.49	0.69
b	0.45	0.75	0.18	0.3
b1	0.65	0.95	0.26	0.37
C	0.38	0.64	0.15	0.25
C1	0.38	0.64	0.15	0.25
D	6.30	6.70	2.48	2.64
D1	5.10	5.50	2.01	2.17
E	5.30	5.70	2.09	2.24
e	2.3 (typ.)		0.91 (typ.)	
e1	4.4	4.8	1.73	1.89
L	7.4	8.0	2.91	3.15

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	600	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current -Continuous (TC=25°C)	2	A
	Drain Current -Continuous (TC=100°C)	1.1	A
I _{DM}	Drain Current Pulsed	7.6	A
E _{AS}	Single Pulsed Avalanche Energy	60	mJ
E _{AR}	Repetitive Avalanche Energy	4.4	mJ
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns
P _D	Power Dissipation (TC = 25 °C)	44	W
	- Derate above 25°C	0.35	W/°C
T _J ,T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

- Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Max.	Units
R _{θJC}	Junction-to-Case	2.87	°C/W
R _{θJA}	Junction-to-Ambient	83.3	

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V _{GS}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1 A	--	4.0	4.7	Ω

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D =250μA	600	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V V _{DS} = 480 V, T _C = 125°C	--	--	1 10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

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	Current, Reverse					
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Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
C_{ISS}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $F = 1.0 \text{ MHz}$	--	180	235	pF
C_{OSS}	Output Capacitance		--	20	25	pF
C_{RSS}	Reverse Transfer Capacitance		--	4.3	5.6	pF
$t_{d(on)}$	Turn-On Time	$V_{DS} = 300 \text{ V}, I_D = 2 \text{ A},$ $R_G = 25 \Omega$	--	25	60	ns
t_r	Turn-On Time		--	24	58	ns
$t_{d(off)}$	Turn-Off Delay Time		--	28	66	ns
t_f	Turn-Off Fall Time		--	28	70	ns
Q_g	Total Gate Charge	$V_{DS} = 480 \text{ V}, I_D = 2 \text{ A},$ $V_{GS} = 10 \text{ V}$	--	9.5	13	nC
Q_{gs}	Gate-Source Charge		--	1.6	--	nC
Q_{gd}	Gate-Drain Charge		--	4	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
I_S	Continuous Source-Drain Diode Forward Current		--	--	1.9	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	7.9	
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 2 \text{ A}, V_{GS} = 0 \text{ V}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$I_S = 2 \text{ A}, V_{GS} = 0 \text{ V}$ $diF/dt = 100 \text{ A}/\mu\text{s}$	--	230	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.0	--	μC

Notes ;

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=55\text{mH}, I_{AS}=2.0\text{A}, V_{DD}=50\text{V}, R_G=25\Omega,$ Starting $T_J=25^\circ\text{C}$
3. $I_{SD} \leq 2.0\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS},$ Starting $T_J=25^\circ\text{C}$
4. Pulse Test: Pulse Width $\leq 300 \mu\text{s},$ Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

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Characteristics Curve

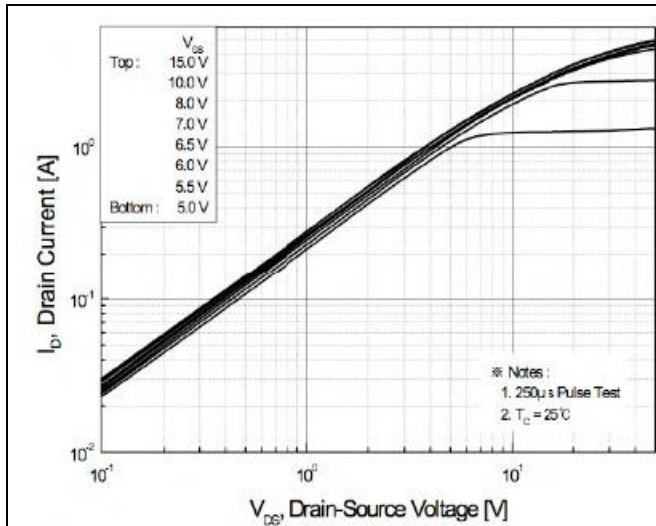


FIG.1-ON REGION CHARACTERISTICS

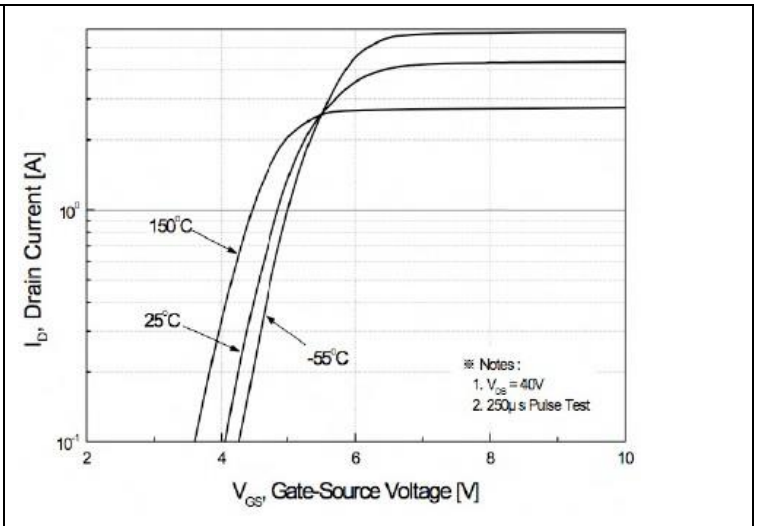


FIG.2-TRANSFER CHARACTERISTICS

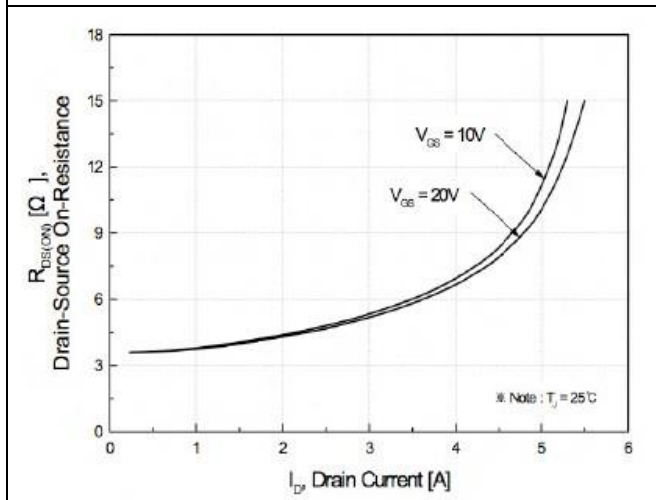


FIG.3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

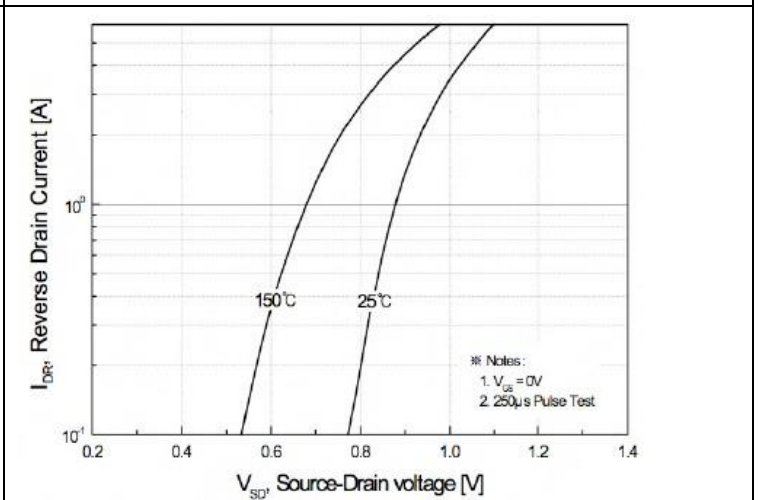


FIG.4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

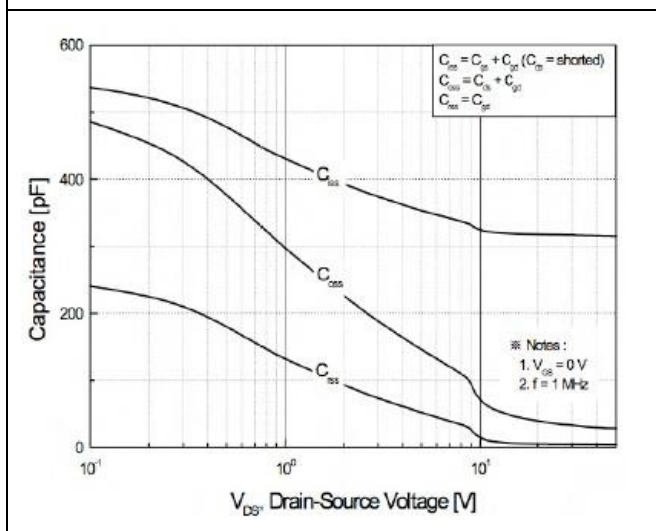


FIG.5-CAPACITANCE CHARACTERISTICS

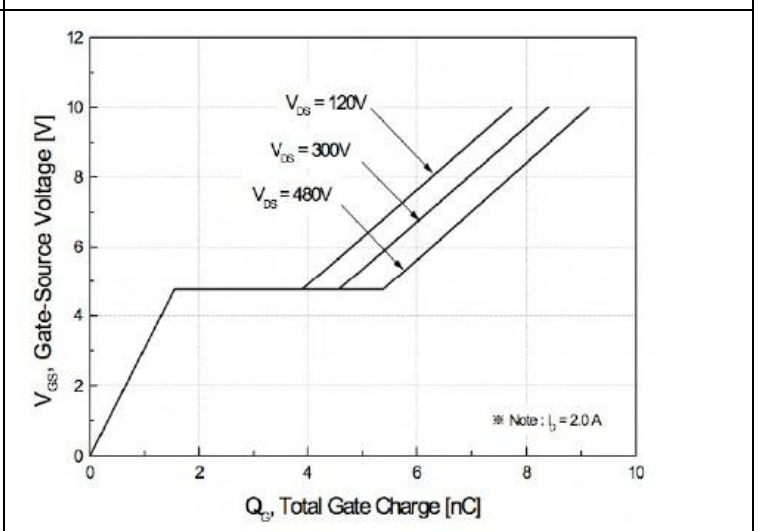


FIG.6-GATE CHARGE CHARACTERISTICS

Characteristics Curve

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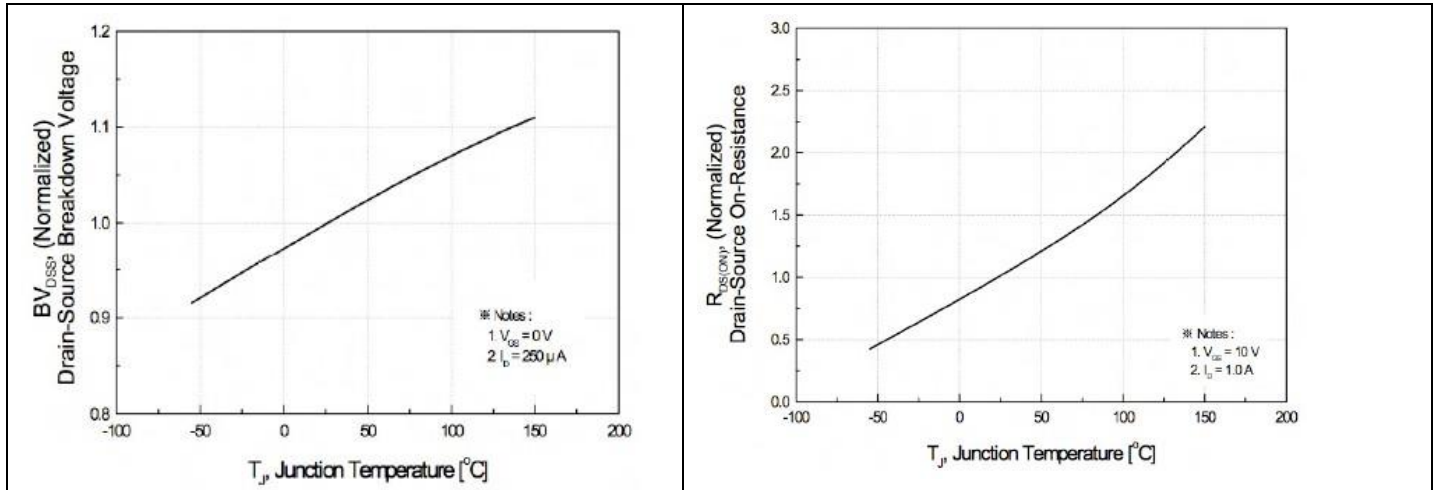


FIG. 7-BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

FIG. 8-ON-RESISTANCE VARIATION VS TEMPERATURE

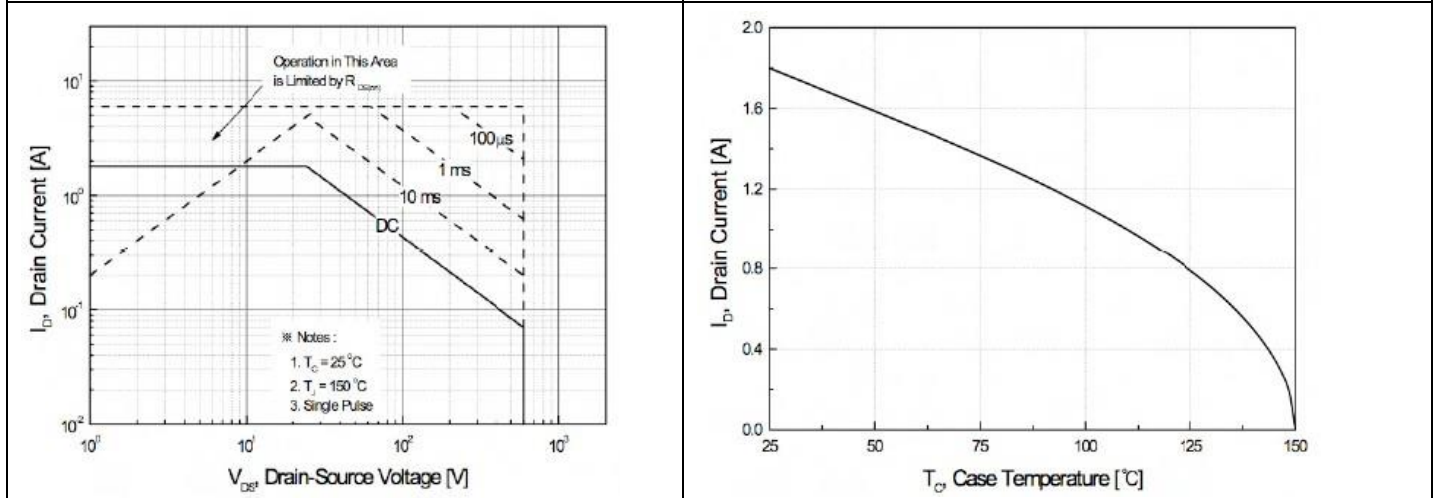


FIG. 9-MAXIMUM SAFE OPERATING AREA

FIG. 10-MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

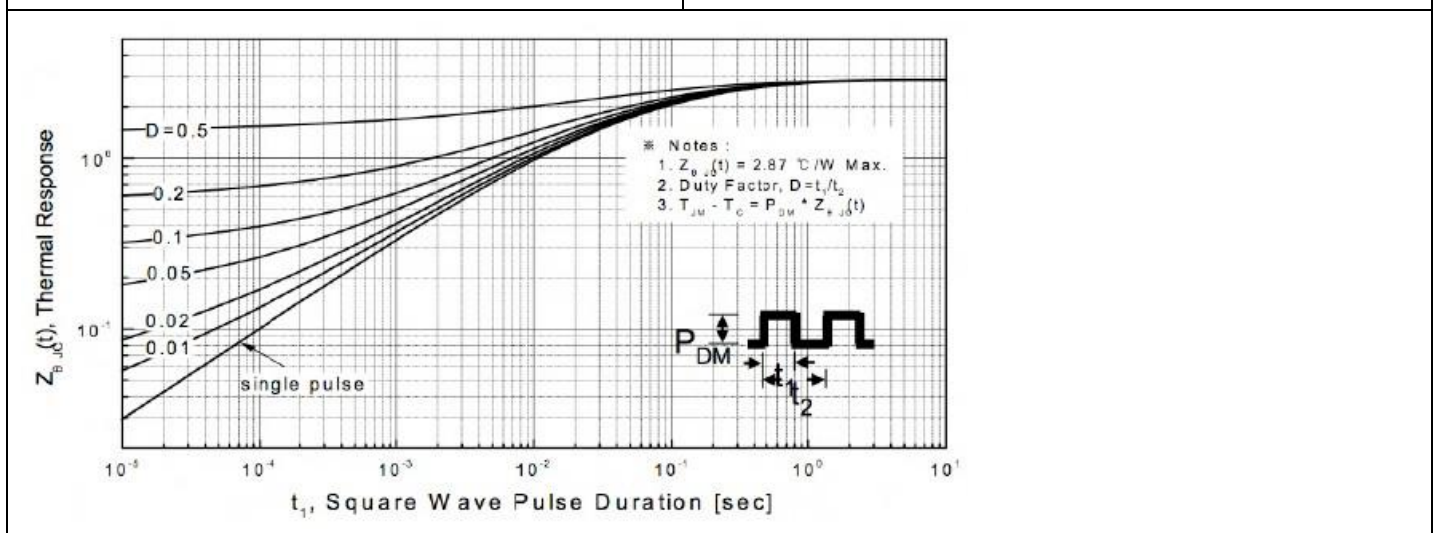


FIG. 11-TRANSIENT THERMAL RESPONSE CURVE

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■ Characteristics Test Circuit & Waveform

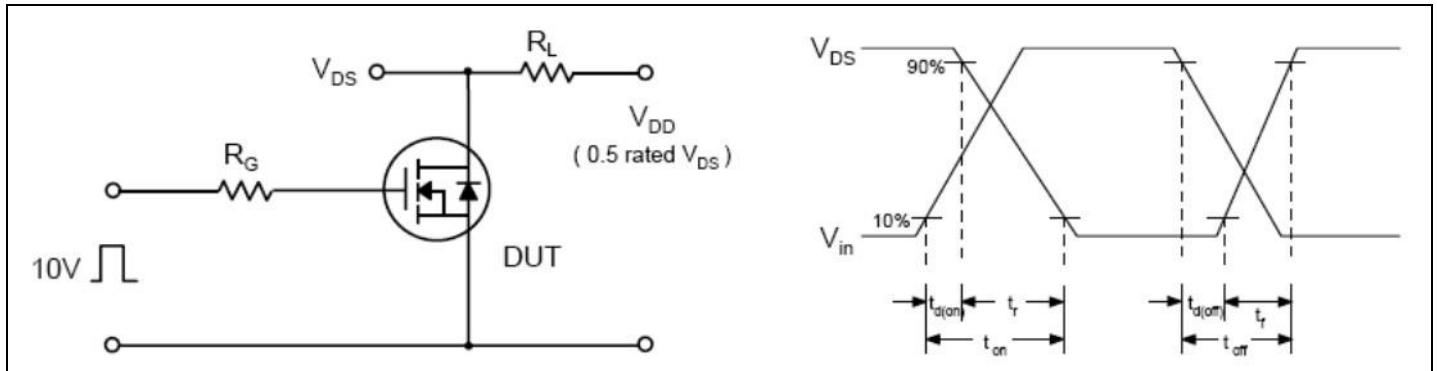


FIG.12-RESISTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

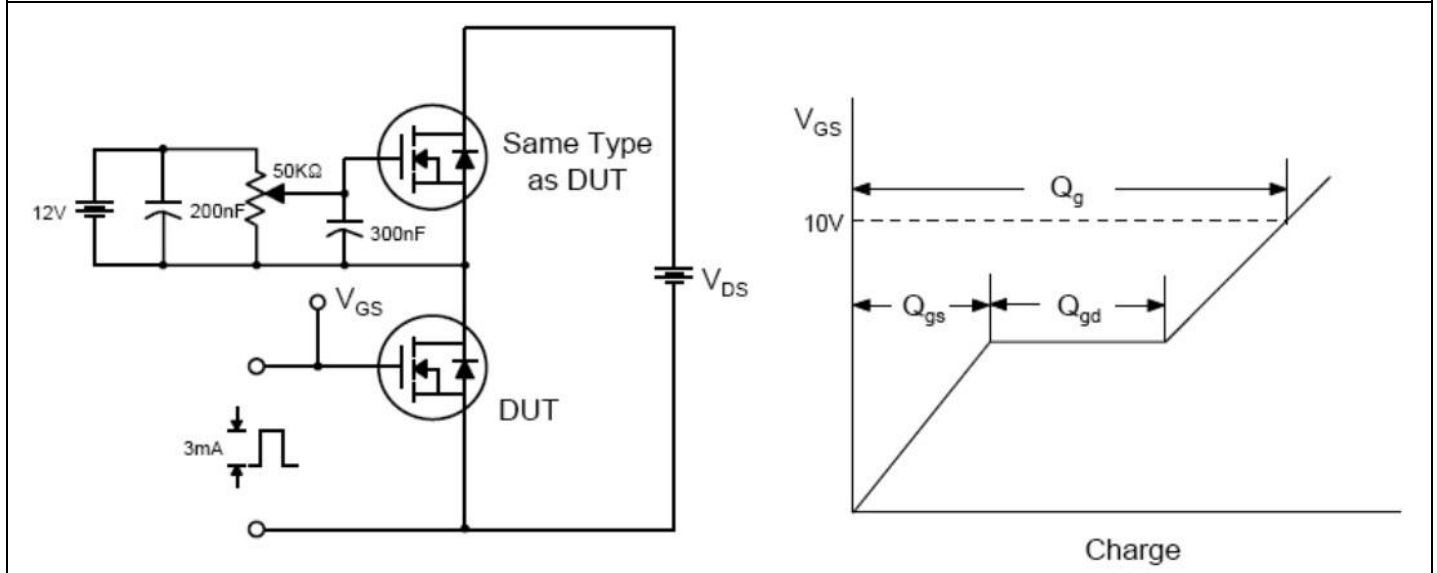


FIG.13-GATE CHARGE TEST CIRCUIT & WAVEFORM

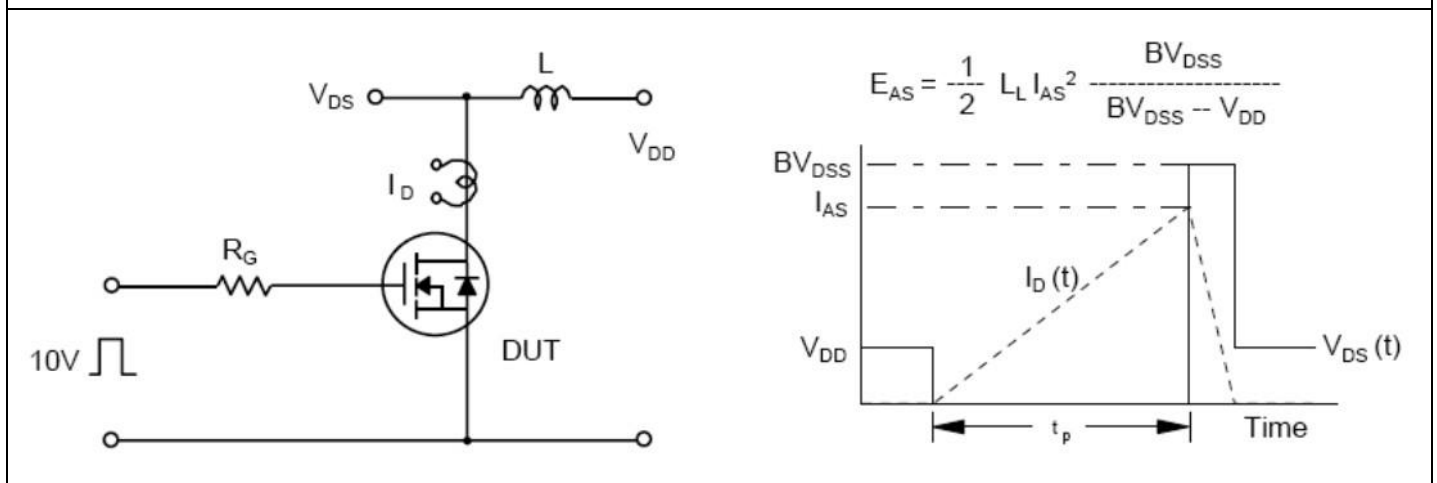


FIG.14-UNCLAMPED LINDUCTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

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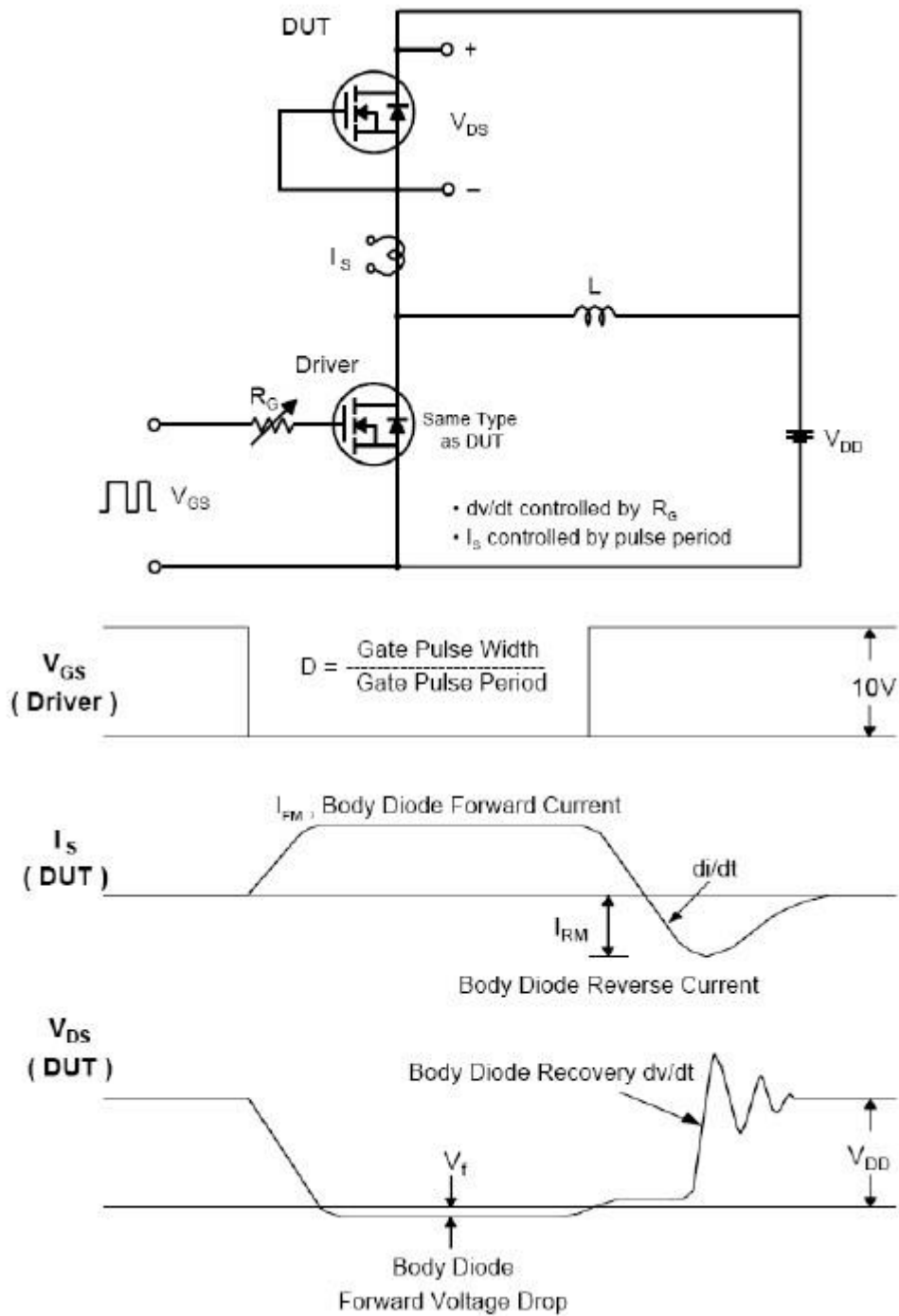


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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